20V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

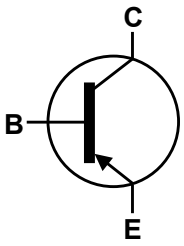
- BV_{CEO} > -20V
- I_C = -2A Continuous Collector Current
- I_{CM} = -4A Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)}$ < -120mV @ -1A
- $R_{CE(SAT)}$ = 40mΩ for a low equivalent on-resistance
- Complimentary NPN Type : DSS20201L
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

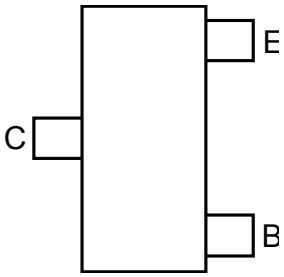
- Case: SOT23
- Case Material: molded plastic, "Green" molding compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (approximate)

SOT23

Top View



Device Symbol



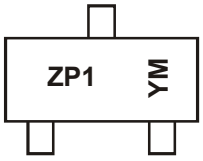
Top View
Pin-Out

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS20200L-7	ZP1	7	8	3,000
DSS20200L-13	ZP1	13	8	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZP1 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-7	V
Peak Pulse Collector Current	I_{CM}	-4	A
Continuous Collector Current	I_C	-2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	600	mW
	(Note 6)		1.2	
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{\theta JA}$	209	°C/W
	(Note 6)		104	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{\theta JL}$	75	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.
7. Thermal resistance from junction to solder-point (at the end of collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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Thermal Characteristics and Derating information

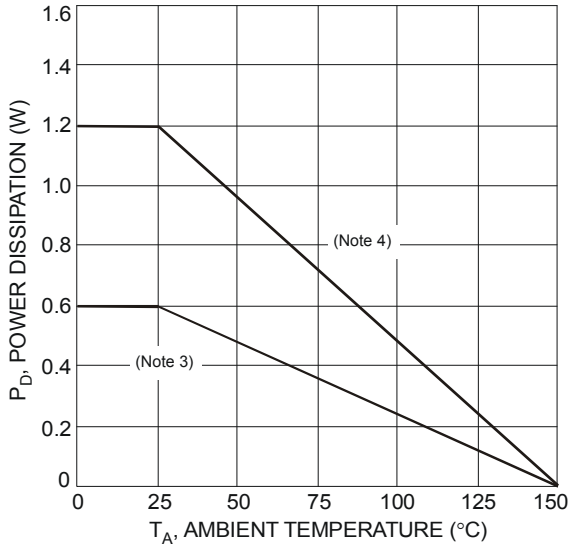

Figure 1 Power Dissipation vs. Ambient Temperature

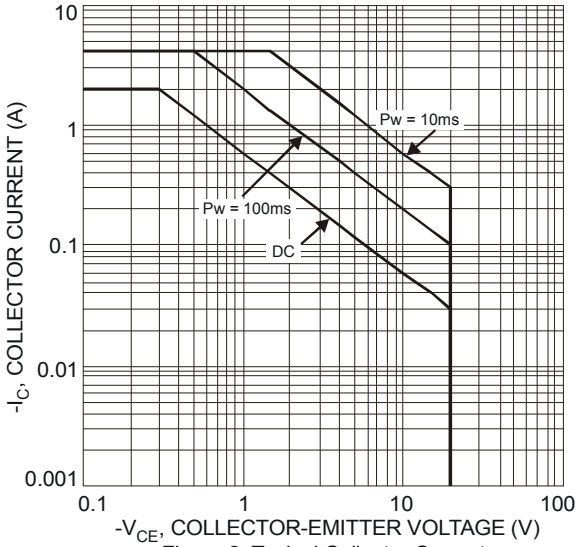

Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

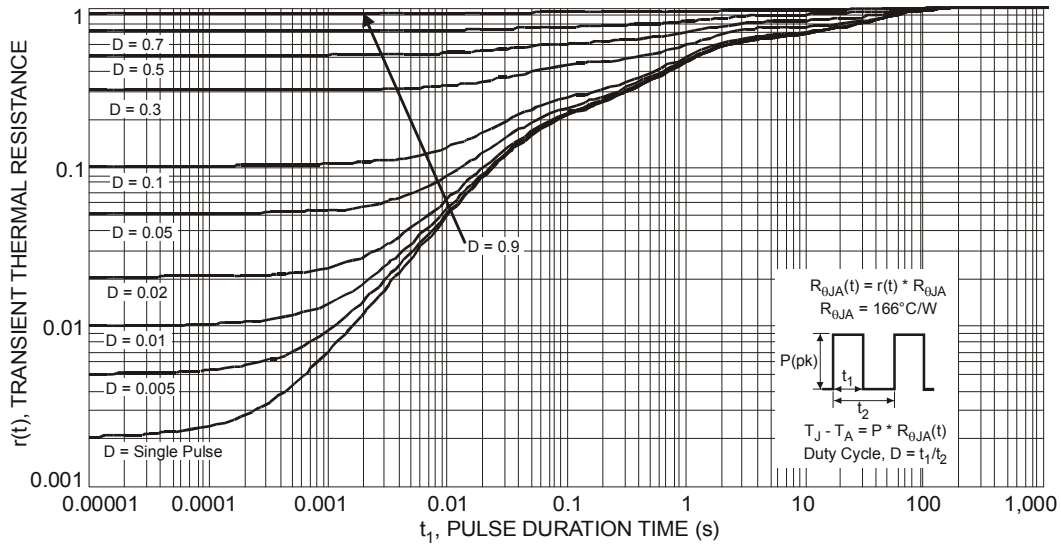

Figure 3 Transient Thermal Response

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-20	—	—	V	I_C = -100µA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	-20	—	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	—	—	V	I_E = -100µA
Collector-Base Cutoff Current	I_{CBO}	—	—	-100	nA	V_{CB} = -20V, I_E = 0
Emitter-Base Cutoff Current	I_{EBO}	—	—	-100	nA	V_{EB} = -7V, I_C = 0
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h_{FE}	250	—	—	—	V_{CE} = -2V, I_C = -10mA
		250	—	—		V_{CE} = -2V, I_C = -500mA
		180	—	—		V_{CE} = -2V, I_C = -1A
		150	—	—		V_{CE} = -2V, I_C = -2A
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	-13	mV	I_C = -0.1A, I_B = -10mA
		—	-50	-90		I_C = -1A, I_B = -100mA
		—	-100	-120		I_C = -1A, I_B = -10mA
		—	-80	-180		I_C = -2A, I_B = -200mA
Equivalent On-Resistance	$R_{CE(SAT)}$	—	40	90	mΩ	I_C = -2A, I_B = -200mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	-0.9	V	I_C = -1A, I_B = -10mA
Base-Emitter Turn-on Voltage	$V_{BE(ON)}$	—	—	-0.9	V	V_{CE} = -2V, I_C = -1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	100	—	—	MHz	V_{CE} = -5V, I_C = -100mA, f = 100MHz
Output Capacitance	C_{obo}	—	—	100	pF	V_{CB} = -3V, f = 1MHz
Input Capacitance	C_{ibo}	—	—	330	pF	V_{EB} = -0.5V, f = 1MHz
SWITCHING CHARACTERISTICS						
Turn-On Time	t_{on}	—	—	180	ns	V_{CC} = -15V, I_C = -750mA, I_{B1} = -15mA
Delay Time	t_d	—	—	60	ns	
Rise Time	t_r	—	—	120	ns	
Turn-Off Time	t_{off}	—	—	430	ns	V_{CC} = -15V, I_C = -750mA, I_{B1} = I_{B2} = -15mA
Storage Time	t_s	—	—	300	ns	
Fall Time	t_f	—	—	130	ns	

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

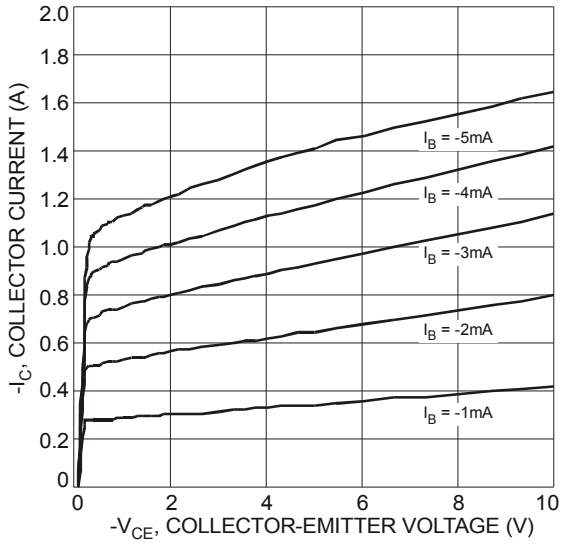

Figure 4 Typical Collector Current vs. Collector-Emitter Voltage

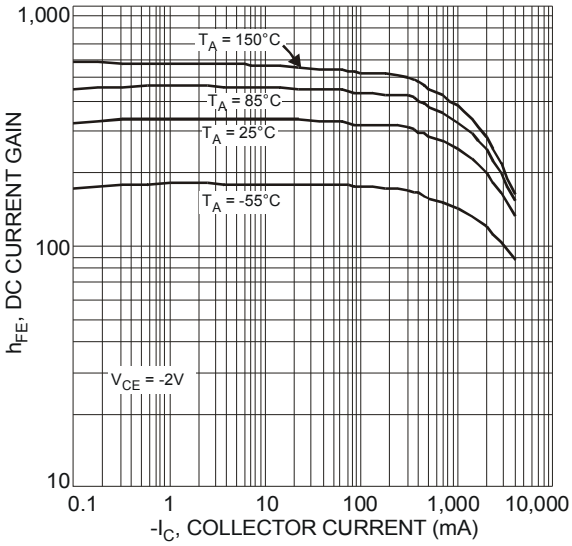

Figure 5 Typical DC Current Gain vs. Collector Current

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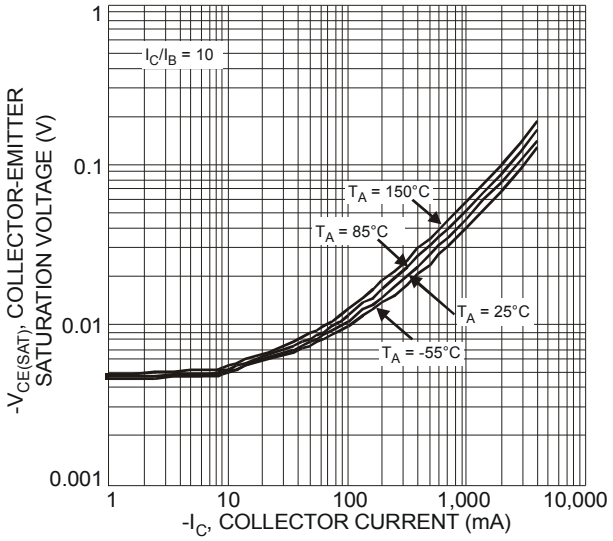

Figure 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

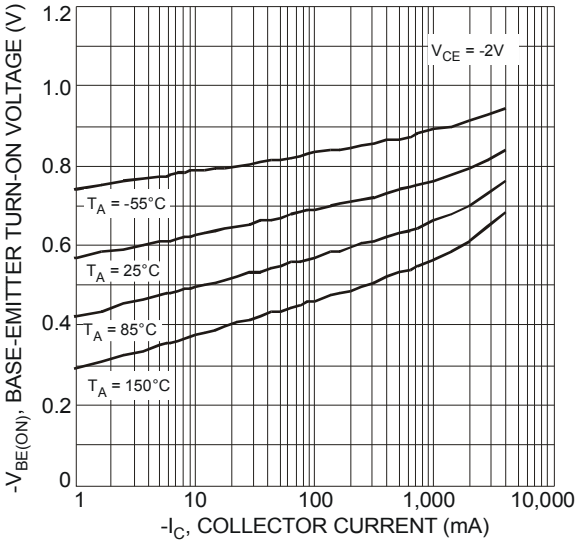

Figure 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current

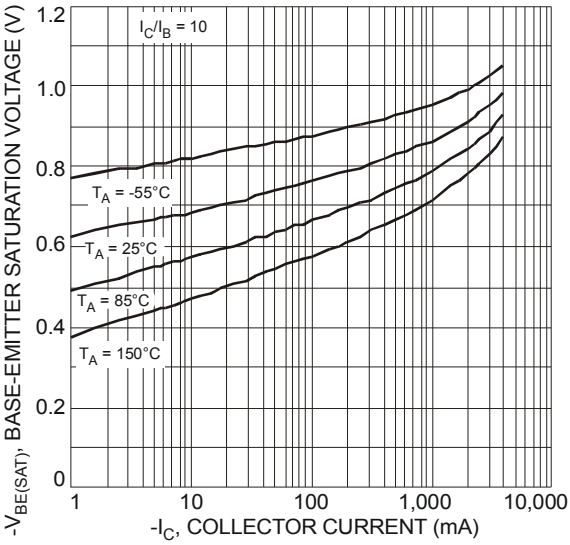

Figure 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

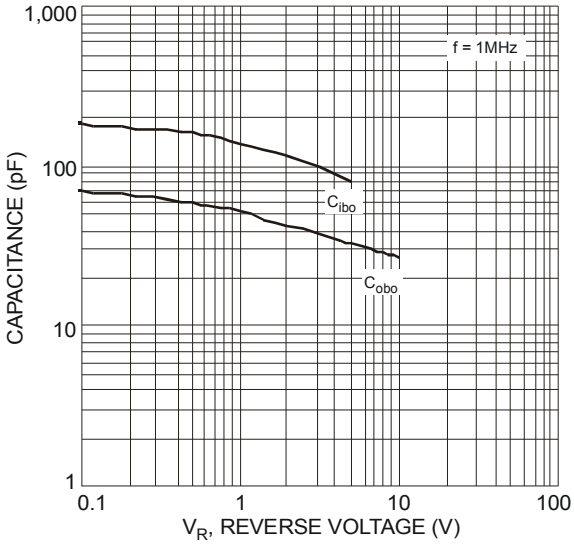

Figure 9 Typical Capacitance Characteristics

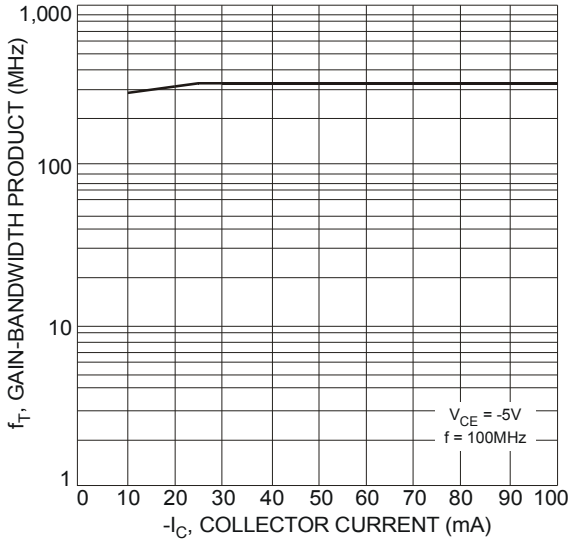

Figure 10 Typical Gain-Bandwidth Product vs. Collector Current

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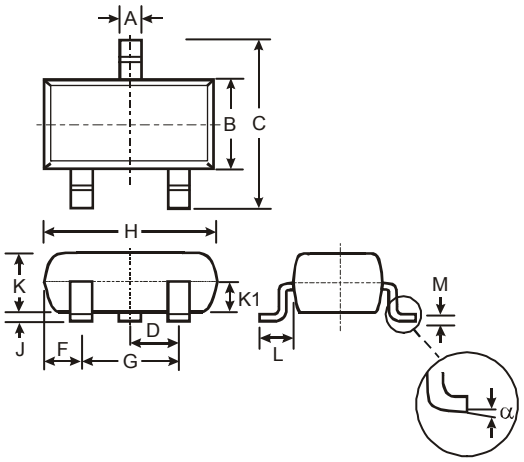
Package Outline Dimensions

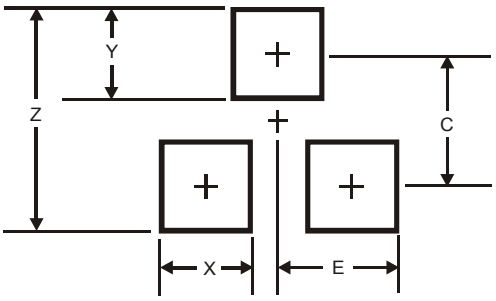
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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